

**Metric Prefixes**

peta	P	$10^{15}$	1 000 000 000 000 000
tera	T	$10^{12}$	1 000 000 000 000
giga	G	$10^9$	1 000 000 000
mega	M	$10^6$	1 000 000
kilo	k	$10^3$	1 000
hecto	h	$10^2$	100
deca	da	$10^1$	10
one		$10^0$	1
deci	d	$10^{-1}$	0.1
centi	c	$10^{-2}$	0.01
milli	m	$10^{-3}$	0.001
micro	$\mu$	$10^{-6}$	0.000 001
nano	n	$10^{-9}$	0.000 000 001
pico	p	$10^{-12}$	0.000 000 000 001
femto	f	$10^{-15}$	0.000 000 000 000 001

**De Morgan's Laws**

- $\overline{AB} = \overline{A} + \overline{B}$
- $\overline{A + B} = (\overline{A})(\overline{B})$

**Silicon**

- Si
- P-type:
  - \* doped with material to remove electrons (add electron holes), usually Boron (B), Aluminum (Al), or Gallium (Ga)
- N-type:
  - \* doped with material to add electrons, usually Antimony (Sb), Arsenic (As), or Phosphorous (P)
- Silicon dioxide:  $\text{SiO}_2$
- Polysilicon is just silicon without the crystal structure

**Transistors**

- pMOS:
  - \* has the bubble
  - \* on when input is 0, off when input is 1
- nMOS
  - \* no bubble
  - \* on when input is on, off when input is off
- CMOS: when you combine a nMOS and pMOS network together to make a gate, where one is the compliment of the other
- $V_t$ : Threshold voltage. Nominal voltage below which the transistor is off
  - \* below as in closer to 0, not less
  - \*  $V_t > 0$  for nMOS,  $V_t < 0$  for pMOS
  - \* this is compared to the gate to source voltage,  $V_{gs}$
- regions: (for nMOS)
  - \* accumulation: gate is negatively charged, attracts positive voids in p-substrate, which block flow in the channel
  - \* depletion: small positive charge on gate repels positive voids from channel, forming a depletion below the gate
  - \* inversion: higher positive charge ( $> V_t$ ) is applied to gate, attracting electrons to the channel and allowing flow

**D Flip Flop vs Latch**

- latch is level triggered
- flip flop is edge triggered

**Fabrication**

- n-well: use diffusion or ion implantation
- positive lithography: expose to UV where you want to remove material
- negative lithography: expose to UV where you want to keep material

**Stick Diagram vs Boolean Function**

- TODO
- there is more than one way of making a stick diagram for an expression
  - \* stuff in series could be in different order, for instance
- if you do it manually, you need to check it with tools:
  - \* LVS: Layout Vs Schematic
  - \* DRC: Design Re-Check
  - \* These aren't really needed for designs automatically generated from verilog code, because of course that's correct

**Lithography**

- the process of printing onto a chip at nanometer scale
- generally uses UV light, wavelength around 150nm
  - \* must use fancy tricks to make 10nm features with 150nm light
  - \* would be nice to use even lower wavelength X-rays, but those are hard to focus
- negative lithography: use the lithography mask to cover what you want to keep.
- positive lithography: mask what you want to remove
- a lens is used to focus the light
  - \* ideally, want a point source for the light, but that is not practical
  - \* Optical Proximity Effect: what happens when your focus from the lens is not just right
  - \* results in rounded corners, inaccurate critical dimensions, and shorter wire ends
  - \* can use Optical Proximity Correction to fix: basically over-emphasize all the features, and/or add extra lines at outset

**MOS transitive  $I$ - $V$  Characteristics and Parasitics**

- $I$ - $V$ : current-voltage relationship
- Transistors are not really ideal switches, they have 3 zones of operation: cutoff, linear, saturation
- definitions:
  - $V_{gs}$ : voltage gate to source
  - $V_{gd}$ : voltage gate to drain
  - $V_{ds}$ : voltage source to drain (across the channel)
  - $V_t$ : critical voltage at which transistor is saturated
  - channel: space between the source and drain, where the electrons flow
- remember that the gate is insulated from the area under it by a thin layer of Silicon Dioxide ( $\text{SiO}_2$ )
- by convention, the source is the terminal at lower voltage
- **cutoff**:
  - \* when  $V_{gs} < 0$
  - \* electrons on the gate attract positive voids in the silicon below, and inhibit current flow. Therefore, the transistor is closed.
  - \*  $I_{ds} = 0$
- **linear**:
  - \*  $V_{gs} > V_t, V_{gd} = V_{gs}, V_{ds} = 0$  or  $V_{gs} > V_t, V_{gs} > V_{gd} > V_t, 0 < V_{ds} < V_{gs} - V_t$
  - \*  $I_{ds}$  linearly proportional to  $V_{ds}$
  - \* channel of electrons forms, allowing current to flow
- **saturated**:
  - \*  $V_{gs} > V_t, V_{gd} < V_t, V_{ds} > V_{gs} - V_t$
  - \* channel pinches off due to electrons attracting to source
  - \*  $I_{ds}$  is independent of  $V_{ds}$

**capacitor effect**

- gate and channel can have a parallel plate capacitor effect, with the thin layer of  $\text{SiO}_2$  acting as the insulator
- $C = \frac{Q}{V} = \epsilon_{\text{SiO}_2} w l / t_{\text{SiO}_2}, V = V + g c - V_t = (v_{gs} - V_{ds}/2) - V_t$

- \*  $l, w$ : length, width of section of gate above channel
- \*  $\epsilon_{SiO_2}$ : permittivity of  $SiO_2$  layer
- \*  $t_{SiO_2}$ : thickness of  $SiO_2$  layer
- general capacitance per unit area:  $C_{ox} = \frac{\epsilon_{ox}}{t_{ox}}$
- \*  $\epsilon_{ox}$ : permittivity of oxidation layer
- \*  $t_{ox}$ : thickness of oxidation layer
- carrier velocity: velocity of the electrons?
- \* proportional to the electric field running horizontally between source and drain
- \*  $v = \mu E, E = V_{ds}/L, t = L/v = L/(\mu E) = L/(\mu \frac{V_{ds}}{L})$
- $\mu$ : mobility. electrons move about twice as fast as positive voids
- $L$ : length of channel
- actual velocity of electrons is the speed of light, but they don't travel in a straight line, they travel atom-to-atom
- \* this slowdown is called the **scattering** effect

### Shockley model of transistor

- $V_{dsat} = V_{gs} - V_t$
- 1st order model:  $\beta = \mu C_{SiO_2} \frac{w}{l}$
- $V_{gs} < V_t$        $I_{ds} = 0$       cutoff
- $V_{ds} < V_{dsat}$        $I_{ds} = \beta(V_{gs} - V_t - \frac{V_{ds}}{2})V_{ds}$       linear
- $V_{ds} > V_{dsat}$        $I_{ds} = \frac{\beta}{2}(V_{gs} - V_t)^2$       saturation
- Must be able to derive this model on exam!

### Non-Ideal $I$ - $V$ Effects

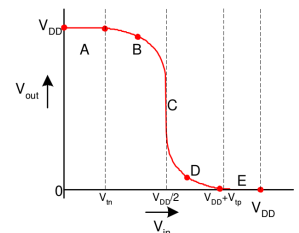
- velocity saturation (due to scattering)
- \* also called short channel effect
- \* this is hard to make into a mathematical formula
- sub-threshold leakage, junction leakage, gate tunneling
- **Body Effect**
- \* affected by  $V_{sb}$ : voltage of the p-substrate (which should be ground)
- \*  $V_t = V_{t0} + \lambda(\sqrt{|-2\phi_F + V_{sb}|} - \sqrt{|-2\phi_F|})$
- $V_{t0}$ : threshold without body bias
- $\phi_F$ : Fermi potential
- negative for nMOS, positive for pMOS
- $\lambda$ : body effect coefficient
- positive for nMOS, negative for pMOS (reversed)
- \* generally fixed/caused by biasing
- \* Forward Body Bias (FBB):
- $V_{sb} < 0, V_t < V_{s0}$
- gates switch faster, but leak more current
- \* Reverse Body Bias (RBB):
- $V_{sb} > 0, V_t > V_{s0}$
- gates switch slower, but consume less power (because less leakage)
- **Temperature**
- \* higher temperature means higher electron mobility, more leakage, and threshold decreases
- **Diffusion Capacitance**
- \* capacitance on the source/drain:  $C_{sb}, C_{db}$
- source/drain are diffusion nodes
- $C$  is comparable to  $C_g$  (gate) for connected nodes,  $\frac{1}{2}C_g$  for unconnected
- (depends on process)
- \* this is the capacitance we care most about (because we must fill it every time the gate switches?)
- \* if two capacitors share a source/drain, that reduces diffusion capacitance (reducing this is a good thing)
- \* also, you can remove unconnected diffusion spots

### DC Response

- example: inverter
- must settle to  $I_{dsn} = |I_{dsp}|$
- $V_{tn}, V_{tp}$ : threshold voltages for nMOS and pMOS (defined in Non-Ideal  $I$ - $V$  Effects)

- $V_{in} = V_{DD} \rightarrow V_{out} = 0, V_{in} = 0 \rightarrow V_{out} = V_{DD}$
- nMOS
- \*  $V_{gsn} = V_{in}, V_{dsn} = V_{out}$
- \* cutoff:  $V_{in} < V_{tn}$
- \* linear:  $V_{in} > V_{tn}, V_{out} < V_{in} - V_{tn}$
- \* saturated:  $V_{in} > V_{tn}, V_{out} > V_{in} - V_{tn}$
- pMOS
- \*  $V_{gsp} = V_{in} - V_{DD}, V_{dsp} = V_{out} - V_{DD}, T_{tp} < 0$
- \* cutoff:  $V_{in} > V_{DD} + V_{tp}$
- \* linear:  $V_{in} < V_{DD} + V_{tp}, V_{out} > V_{in} - V_{tp}$
- \* saturated:  $V_{in} < V_{DD} + V_{tp}, V_{out} < V_{in} - V_{tp}$
- to calculate actual output voltage, balance  $I_{dsn} = I_{dsp}$  (easiest to do graphically)
- \* end up with a graph of  $V_{out}$  as function of  $V_{in}$

Region	nMOS	pMOS
A	Cutoff	Linear
B	Saturation	Linear
C	Saturation	Saturation
D	Linear	Saturation
E	Linear	Cutoff



- \* don't want to switch nMOS and pMOS because then nMOS would saturate at far end of graph (and vice versa for pMOS)
- \* horizontal position of graph can be varied by tuning  $\beta_p/\beta_n$
- called beta ratio, or skewed gate
- $\beta_p/\beta_n > 1 \rightarrow$  right,  $\beta_p/\beta_n \rightarrow$  left
- \* unity gain slope: part of response graph where the slope is  $-1$
- want to tune  $\beta_p/\beta_n$  to put logic levels at these regions to maximize noise margins
- \* Noise Margins:
- $NM_H = |V_{OH} - V_{IH}|, NM_L = |V_{OL} - V_{IL}|$
- that's just the higher/lower of the two axes

### Transient Analysis

- for instance, find step response of gate to determine rise time.
- rise/fall delay: time from when  $V_{in}$  crosses  $\frac{V_{DD}}{2}$  to when  $V_{out}$  crosses it
- rise/fall time: (of  $V_{in}$  or  $V_{out}$ ): time for that signal to go from  $0.1V_{DD}$  to  $0.9V_{DD}$  (or reverse)
- TODO many equations and such for inverter step response (from slides)
- TODO pass transistors (from slides)

### Pass Transistors

- for nMOS trying to pass  $V_{DD}$  or pMOS trying to pass 0
- nMOS can pull no higher than  $V_{DD} - V_{tn}$  if  $V_g = V_{DD}$
- \* more generally,  $V_g - V_{tn}$
- \* called degraded 1
- pMOS can pull no lower than  $|V_{tp}|$

### Delay

- generally estimated with RC models
- \* for nMOS with width  $k$ :
- \* resistance of  $R/k$
- \* caps of  $kC$  on all terminals
- \* pMOS same except resistance is  $2R/k$
- depends on effective  $R$  and  $C$  of transistors
- \* exactly what parasitic caps depends on exact layout (which stuff is shared between transistors)
- width:
- \*  $C$  proportional to width (approx  $2 \text{ fF}/\mu\text{m}$ )
- \*  $R$  inversely proportional to width (approx  $6 \text{ k}\Omega \cdot \mu\text{m}$ )
- \* TODO unity transistors
- find widths necessary for rise and fall resistance to be same as standard inverter

- \* pMOS is about half as conductive as nMOS, so the inverter has nMOS=1, pMOS=2
- \* larger width  $\rightarrow$  smaller  $R$
- \* transistors in series: delay adds, so double the width
- \* transistors in parallel: same as a single transistor (because we assume worst case of only one being active)
- use effective resistance in RC model:  $I_{ds} = V_{ds}/R$  (just good enough for a RC model, not for current at arbitrary time)
- find delay of circuit
  - \* decompose to RC model (take into account widths of each transistor)
    - replace transistors with resistors
    - add parasitic caps on either side of every transistor (cap value = width of transistor)
      - caps with both pins short to ground don't count, are never charged
      - caps from  $V_{DD}$  to ground don't count, always charged
  - \* add together all R and C's to get delay
    - don't count  $R$  of nMOS and pMOS at the same time, because they're never on at the same time
- Elmore Delay:
  - \* ON transistors look like resistors, so pullup/pulldown network is modeled as RC ladder
  - \*  $t = \sum_{i \in \text{nodes}} R_{i \rightarrow \text{source}} C_i$   
 $= R_1 C_1 + (R_1 + R_2) C_2 + \dots + (R_1 + \dots + R_n) C_n$
- Contamination delay: just best case delay (smallest delay)
  - \* in this case, you'll count parallel transistors as parallel resistors

## Power Estimation